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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	2822 2822
	Examiner Name	2822 K. DUONG
Sheet 1 of 8		Attorney Docket No: 303.412US4

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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John H. Duong

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Complete if Known

Application Number	Unknown
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First Named Inventor	Noble Jr., Wendell
Group Art Unit	XXXXXX
Examiner Name	XXXXXX

Sheet 2 of 8

Attorney Docket No: 303.412US4

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	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	2000/0000
	Examiner Name	2000/0000
Sheet 3 of 8		Attorney Docket No: 303.412US4

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
KBD	JP-2000-164883	06/16/2000	Yamazaki, S., et al.	H01L	29/786	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
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Filing Date	Even Date Herewith
First Named Inventor	Noble Jr., Wendell
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 4 of 8

Attorney Docket No: 303.412US4

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	<i>Wendell Noble Jr.</i>
	Examiner Name	<i>Wendell Noble Jr.</i>
Sheet 5 of 8	Attorney Docket No: 303.412US4	

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Noble Jr., Wendell
Group Art Unit	<i>2122</i>
Examiner Name	<i>2122</i>

Sheet 6 of 8

Attorney Docket No: 303.412US4

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	2166/001
	Examiner Name	2166/001
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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	1000/000
	Examiner Name	1000/000
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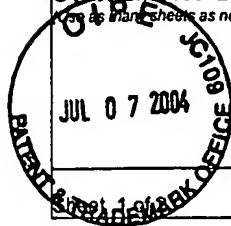
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Application Number	10/738,449
Filing Date	December 16, 2003
First Named Inventor	Noble Jr., Wendell
Group Art Unit	2822 2822
Examiner Name	John K. Duong K. DUONG

Attorney Docket No: 303.412US4

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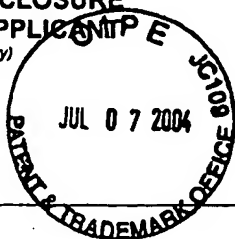
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Application Number	10/738,449
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First Named Inventor	Noble Jr., Wendell
Group Art Unit	2222
Examiner Name	Patricia

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